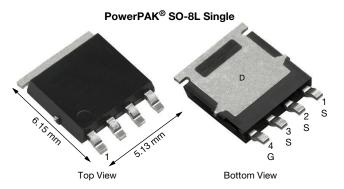
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Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	100			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0110			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0140			
I _D (A)	32			
Configuration	Single			

FEATURES

- TrenchFET[®] Power MOSFET
- AEC-Q101 Qualified^d
- 100 % R_g and UIS Tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

N-Channel MOSFET



RoHS COMPLIANT HALOGEN FREE

V _{DS} (V)	100
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ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ402EP (for detailed order number please see <u>www.vishay.com/doc?79771</u>)

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unles	s otherwise noted	4)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current ^a	T _C = 25 °C	1-	32	
Continuous Drain Currents	T _C = 125 °C	I _D	32	
Continuous Source Current (Diode Conduction) ^a		IS	32	А
Pulsed Drain Current ^b		I _{DM}	75	
Single Pulse Avalanche Current		I _{AS}	31	
Single Pulse Avalanche Energy		E _{AS}	48	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	P	83	W
Maximum Power Dissipation~	sipation ^D P_D 27		VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) ^{e, f}			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	65	°C/W
Junction-to-Case (Drain)		R _{thJC}	1.8	0/10

Notes

a. Package limited

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR-4 material)

d. Parametric verification ongoing

See solder profile (www.vishav.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed e. copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		<u> </u>					
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μΑ	100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	: 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 100 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA
		$V_{GS} = 0 V$	$V_{DS} = 100 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150	1
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 10.7 A	-	0.0090	0.0110	
Drain-Source On-State Resistance ^a	Б	V _{GS} = 10 V	I _D = 10.7 A, T _J = 125 °C	-	-	0.0170	
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 10.7 A, T _J = 175 °C	-	-	0.0210	Ω
		$V_{GS} = 4.5 V$	I _D = 9.5 A	-	0.0115	0.0140	
Forward Transconductanceb	9 _{fs}	V _{DS} =	= 15 V, I _D = 10.7 A	-	54	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	1829	2286	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	722	903	pF
Reverse Transfer Capacitance	C _{rss}			-	62	78	
Total Gate Charge ^c	Qg			-	34	51	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 50 \text{ V}, I_D = 10 \text{ A}$	-	6	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	13	-	
Gate Resistance	Rg		f = 1 MHz	0.65	1.39	2	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	10	15	
Rise Time ^c	t _r	V _{DD}	$= 50 \text{ V}, \text{ R}_{\text{I}} = 5 \Omega$	-	10	15	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 10 \text{ A},$	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	27	40	ns
Fall Time ^c	t _f	1		-	7	11]
Source-Drain Diode Ratings and Char	acteristics ^b				·		
Pulsed Current ^a	I _{SM}			-	-	75	Α
Forward Voltage	V _{SD}	I _F :	$I_{\rm F} = 7 \text{ A}, V_{\rm GS} = 0 \text{ V}$		0.77	1.2	V

Notes

g. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

h. Guaranteed by design, not subject to production testing.

i. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

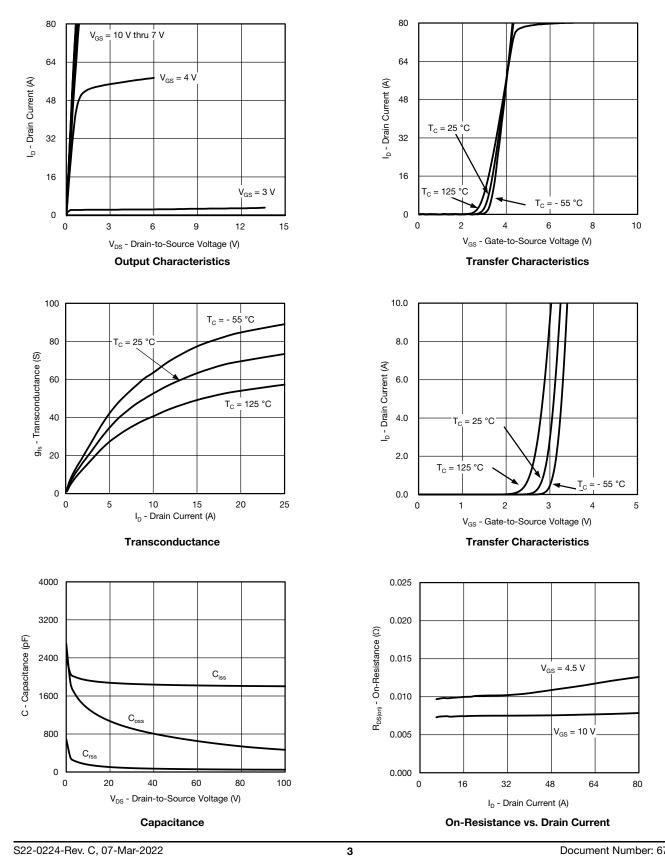
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



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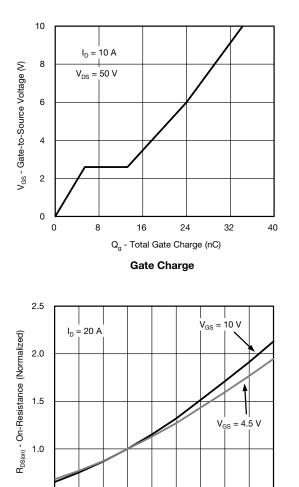
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

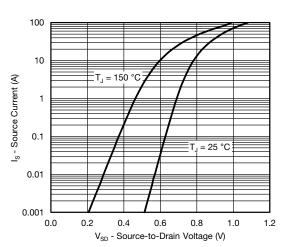
100 125

T_{.1} - Junction Temperature (°C)

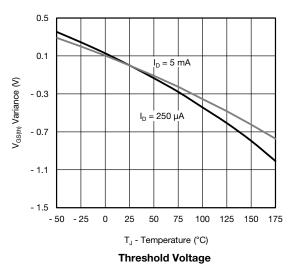
On-Resistance vs. Junction Temperature

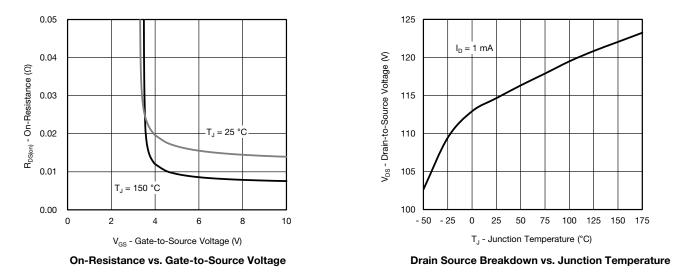
150 175





Source Drain Diode Forward Voltage





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0.5

- 50 - 25

0 25 50 75

4

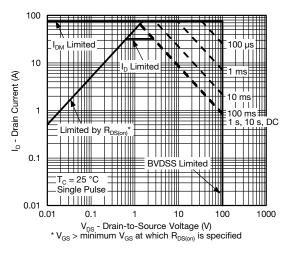
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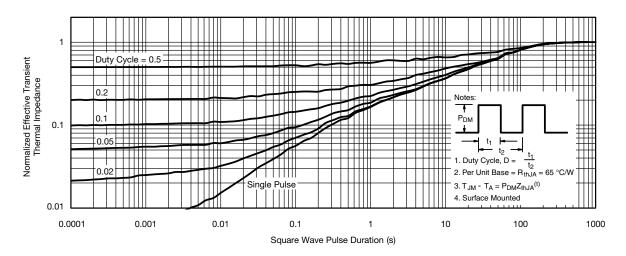


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)





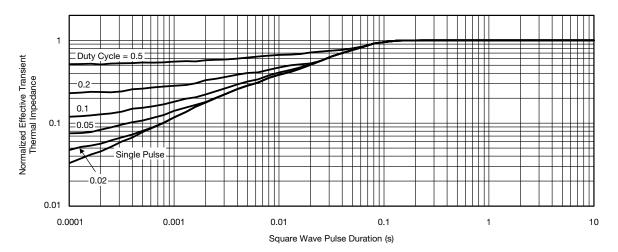


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

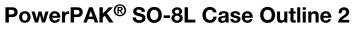
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

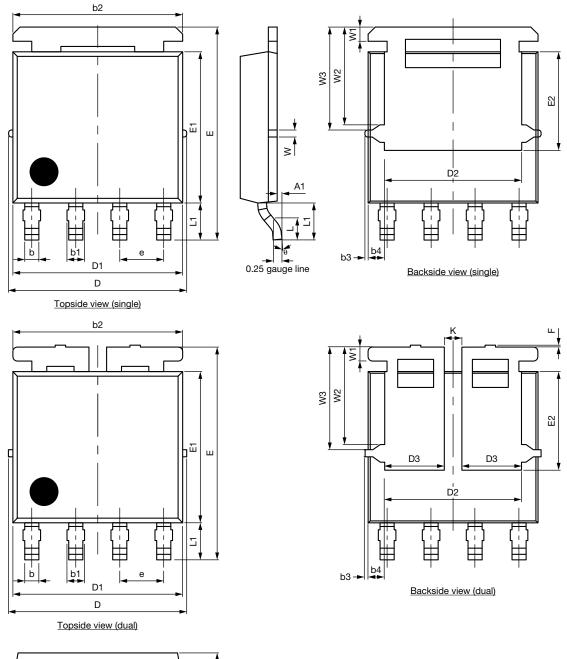
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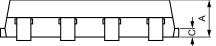
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Package Information



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DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	MIN. NOM.		
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W		0.23			0.009		
W1	0.41			0.016			
W2	2.82			0.111			
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will govern



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RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



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